

## Thermally-Enhanced High Power RF LDMOS FETs 150 W, 420 – 500 MHz

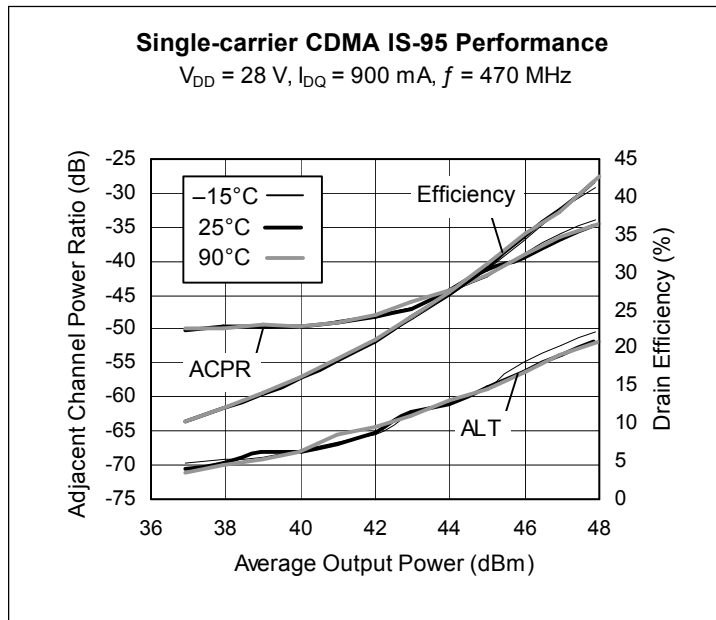
### Description

The PTFA041501GL and PTFA041501HL are 150-watt LDMOS FETs designed for ultra-linear CDMA power amplifier applications. They are available in thermally-enhanced plastic open-cavity packages with copper flanges. Manufactured with Infineon's advanced LDMOS process, these devices provide excellent thermal performance and superior reliability.

PTFA041501GL  
Package PG-63248-2



PTFA041501HL  
Package PG-64248-2



### Features

- Thermally-enhanced plastic open-cavity (EPOC™) packages with copper flanges, Pb-free and RoHS-compliant
- Broadband internal matching
- Typical CDMA performance at 470 MHz, 28 V
  - Average output power = 60 W
  - Linear Gain = 21 dB
  - Efficiency = 41%
- Typical CW performance, 470 MHz, 28 V
  - Output power at P-1dB = 175 W
  - Efficiency = 62%
- Integrated ESD protection: Human Body Model, Class 1 (minimum)
- Excellent thermal stability
- Low HCI drift
- Capable of handling 10:1 VSWR @ 28 V, 150 W (CW) output power

### RF Characteristics

**Single-carrier CDMA IS-95 Measurements** (not subject to production test—verified by design/characterization in Infineon test fixture)

$V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 900\text{ mA}$ ,  $P_{OUT} = 60\text{ W}$  average,  $f = 470\text{ MHz}$

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	—	21	—	dB
Drain Efficiency	$\eta_D$	—	41	—	%
Adjacent Channel Power Ratio	ACPR	—	-33	—	dB

All published data at  $T_{CASE} = 25^\circ\text{C}$  unless otherwise indicated

**ESD:** Electrostatic discharge sensitive device—observe handling precautions!

## RF Characteristics (cont.)

### Two-tone Measurements (tested in Infineon test fixture)

$V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 900\text{ mA}$ ,  $P_{OUT} = 150\text{ W PEP}$ ,  $f = 470\text{ MHz}$ , tone spacing = 1 MHz

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	$G_{ps}$	20.0	21.0	—	dB
Drain Efficiency	$\eta_D$	45.0	46.5	—	%
Intermodulation Distortion	IMD	—	-29	-28	dBc

## DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$ , $I_{DS} = 10\text{ }\mu\text{A}$	$V_{(BR)DSS}$	65	—	—	V
Drain Leakage Current	$V_{DS} = 28\text{ V}$ , $V_{GS} = 0\text{ V}$	$I_{DSS}$	—	—	1.0	$\mu\text{A}$
On-State Resistance	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.07	—	$\Omega$
Operating Gate Voltage	$V_{DS} = 28\text{ V}$ , $I_{DQ} = 900\text{ mA}$	$V_{GS}$	2	2.48	3	V
Gate Leakage Current	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	—	—	1.0	$\mu\text{A}$

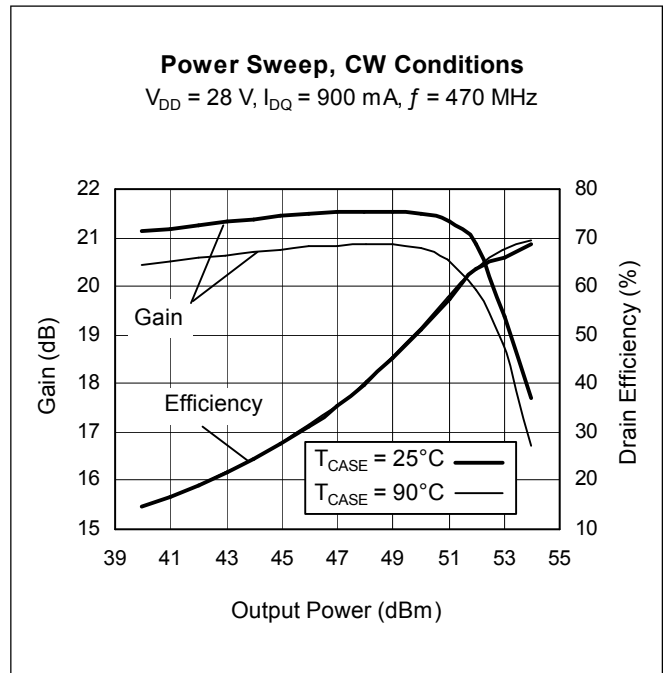
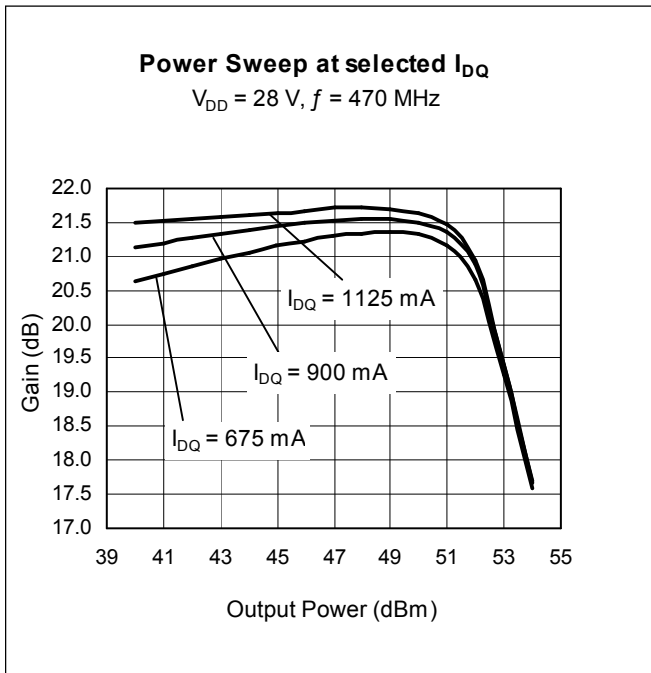
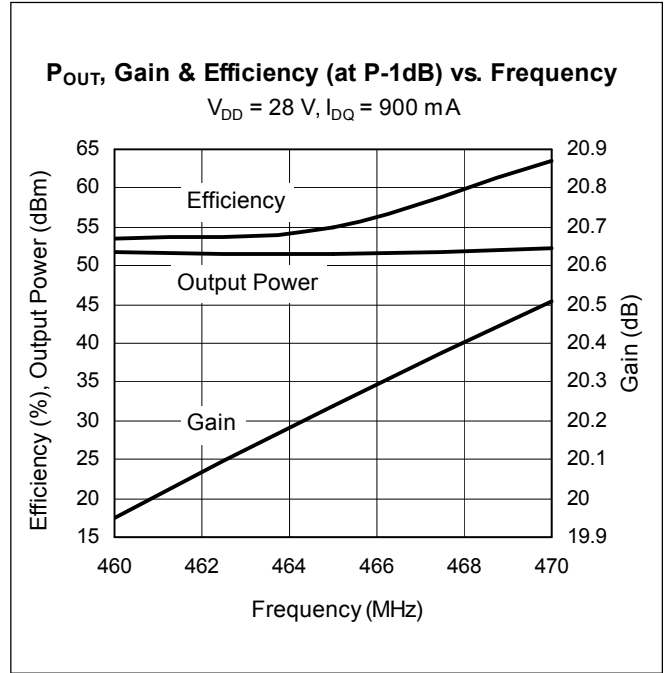
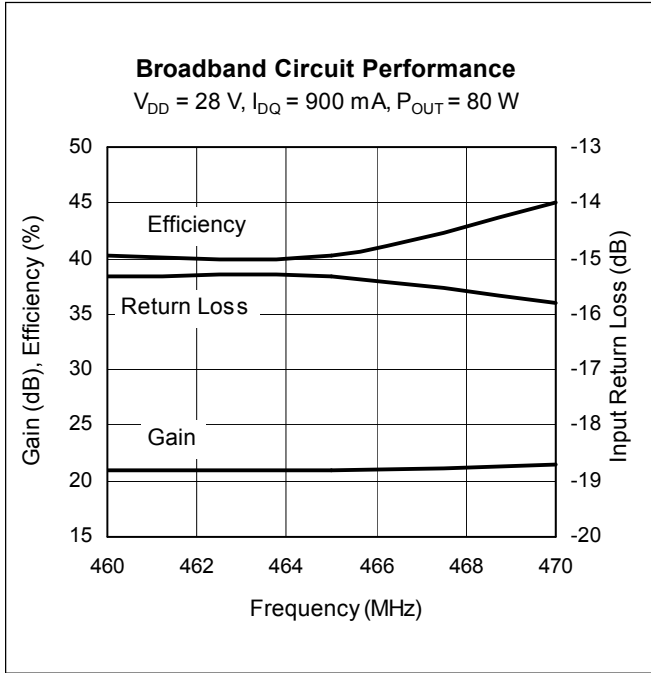
## Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	65	V
Gate-Source Voltage	$V_{GS}$	-0.5 to +12	V
Junction Temperature	$T_J$	200	$^{\circ}\text{C}$
Total Device Dissipation	$P_D$	625	W
Above 25 $^{\circ}\text{C}$ derate by		3.57	W/ $^{\circ}\text{C}$
Storage Temperature Range	$T_{STG}$	-40 to +150	$^{\circ}\text{C}$
Thermal Resistance ( $T_{CASE} = 70^{\circ}\text{C}$ , 150 W CW, soldered)	$R_{\theta JC}$	0.28	$^{\circ}\text{C/W}$

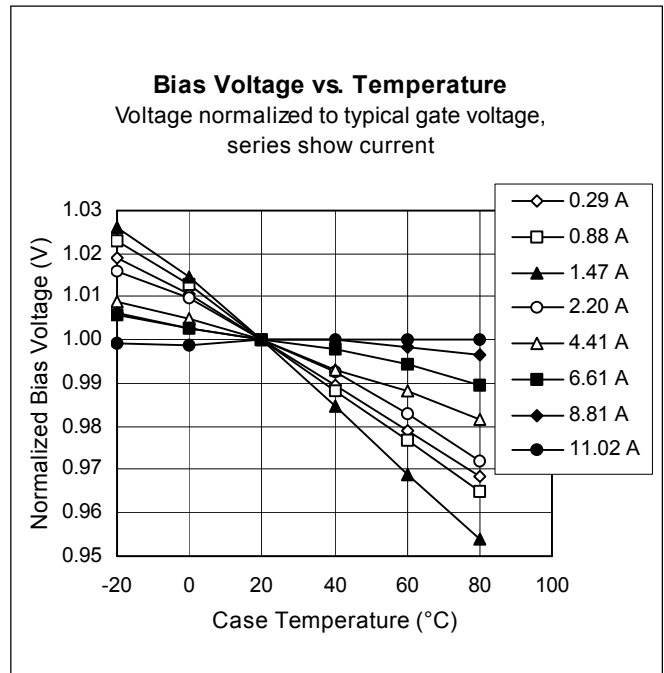
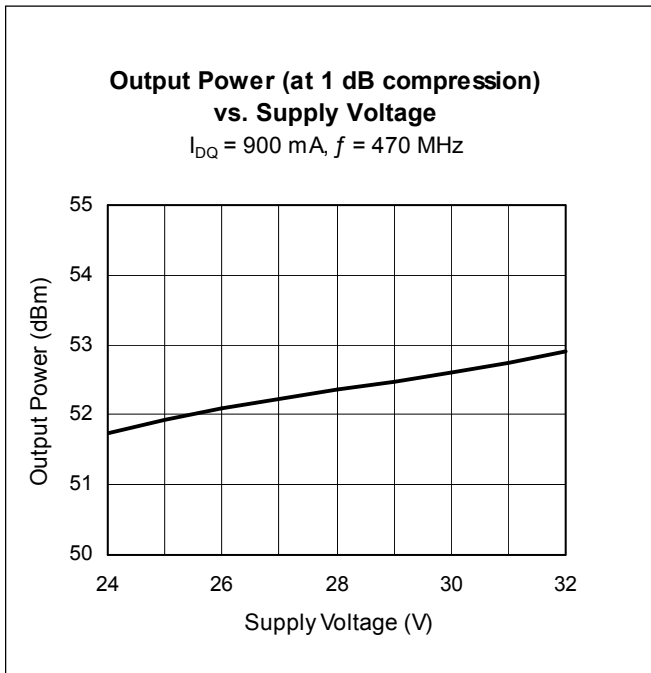
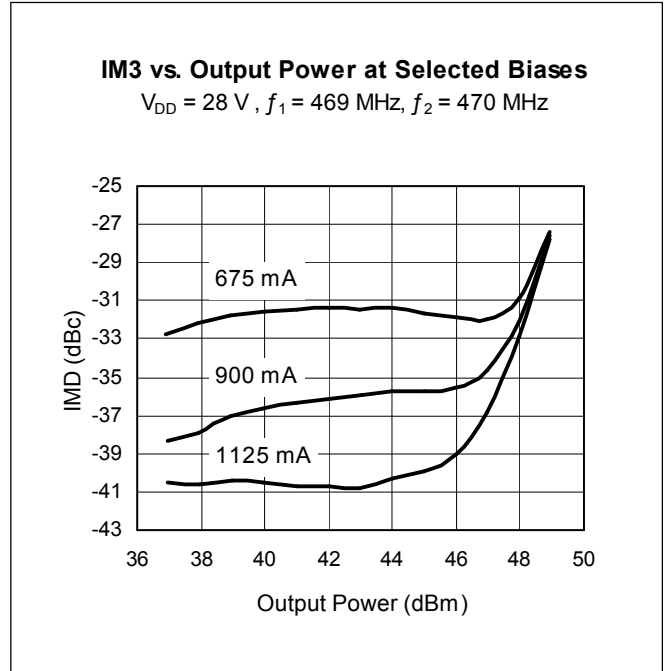
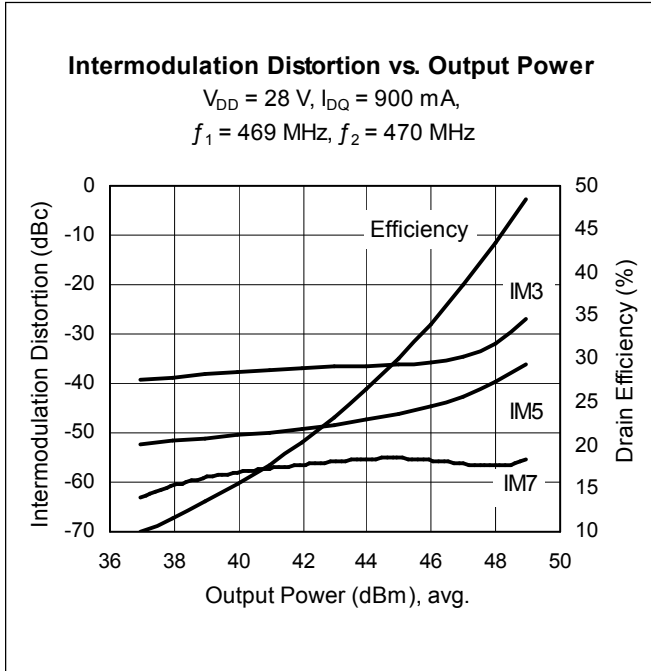
## Ordering Information

Type and Version	Package Type	Package Description	Shipping	Marking
PTFA041501GL V1	PG-63248-2	Thermally-enhanced slotted flange, single-ended	Tray	PTFA041501GL
PTFA041501HL V1	PG-64248-2	Thermally-enhanced slotted flange, single-ended	Tray	PTFA041501HL

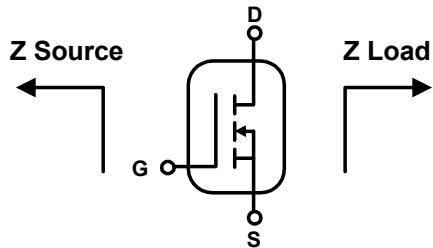
**Typical Performance** (data taken in a production )



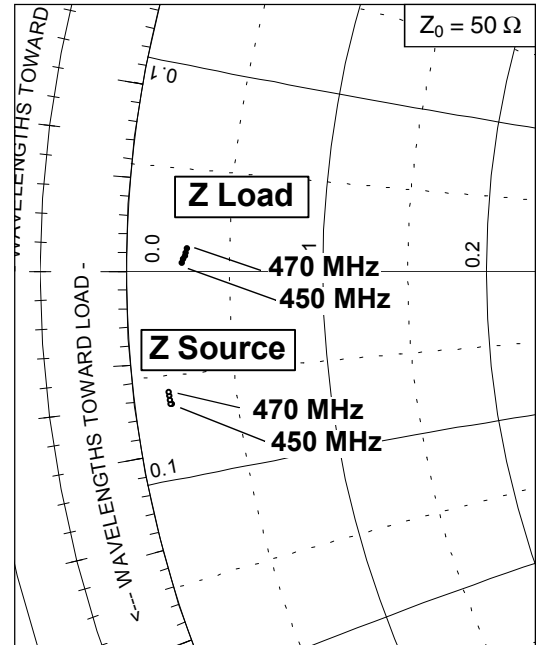
Typical Performance (cont.)



### Broadband Circuit Impedance

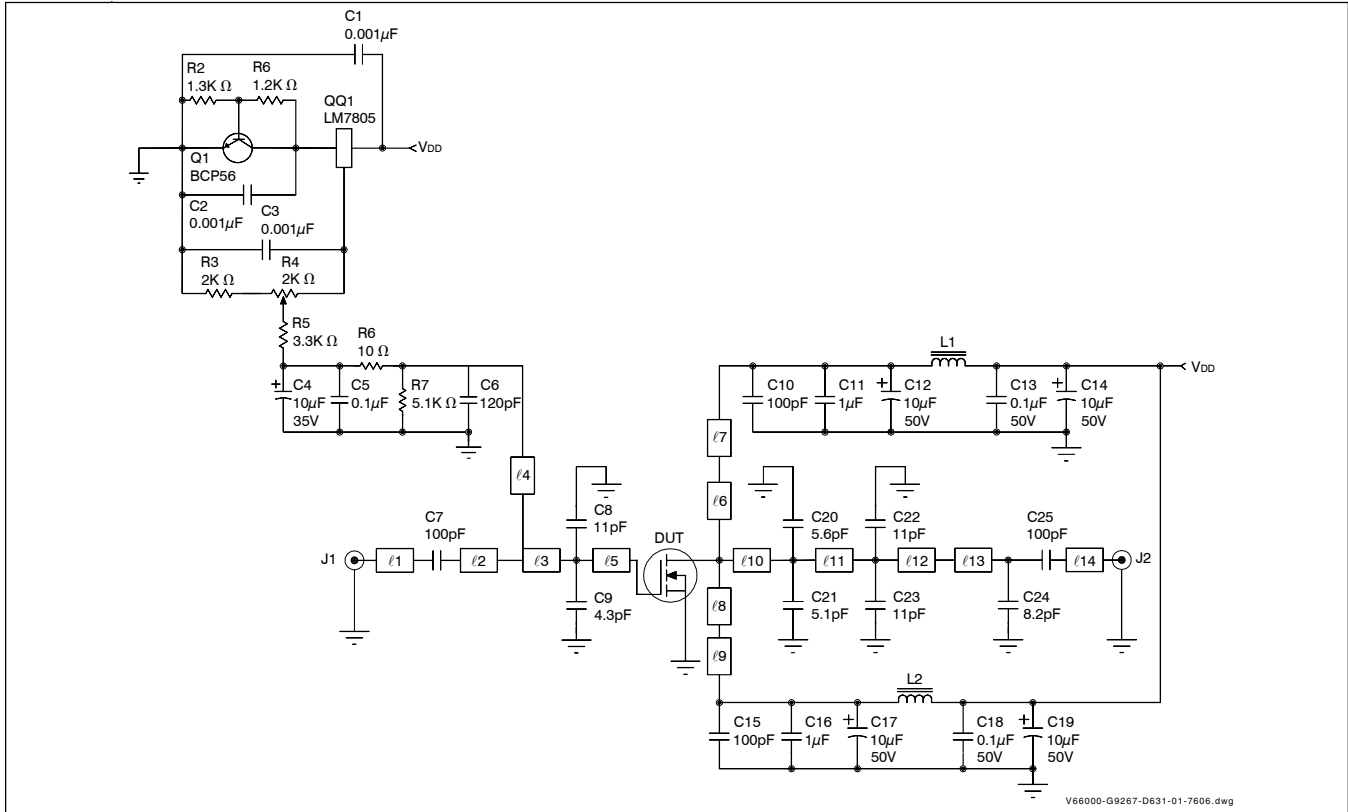


Frequency MHz	Z Source W		Z Load W	
	R	jX	R	jX
450	0.88	-3.20	1.33	0.22
455	0.84	-3.20	1.35	0.31
460	0.84	-3.10	1.40	0.38
465	0.84	-3.00	1.41	0.47
470	0.83	-2.90	1.44	0.57



See next page for circuit information

### Reference Circuit



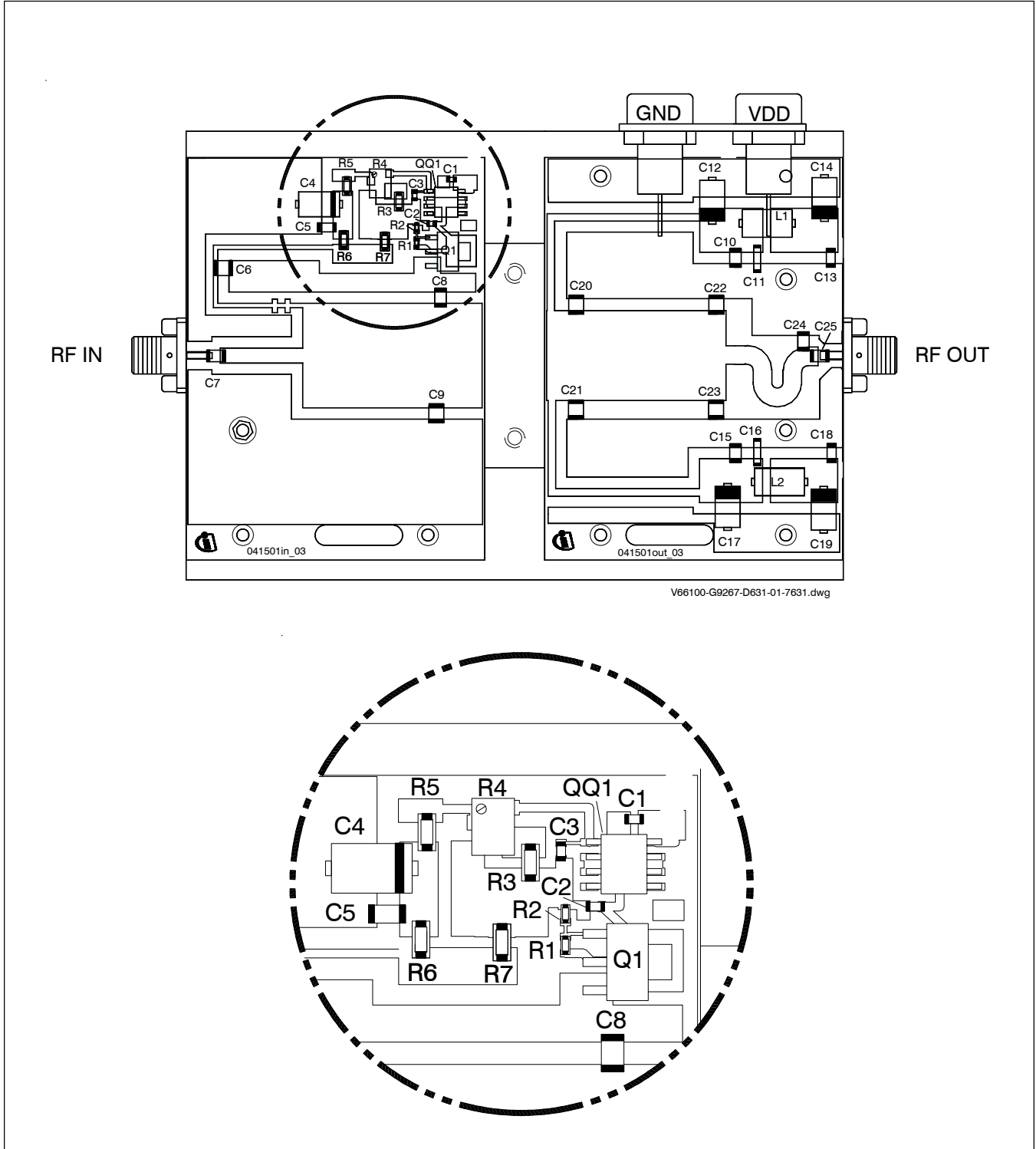
Reference circuit schematic for  $f = 460 \text{ MHz}$

#### Circuit Assembly Information

DUT	PTFA041501GL or PTFA041501HL	LDMOS Transistor	
PCB	0.76 mm [.030"] thick, $\epsilon_r = 9.2$	Rogers TMM10	2 oz. copper

Microstrip	Electrical Characteristics at 460 MHz	Dimensions L x W (mm)	Dimensions L x W (in.)
l 1	0.016 $\lambda$ , 50.69 $\Omega$	4.32 x 0.71	0.170 x 0.028
l 2	0.058 $\lambda$ , 24.34 $\Omega$	14.22 x 2.54	0.560 x 0.100
l 3	0.097 $\lambda$ , 4.85 $\Omega$	21.59 x 17.78	0.850 x 0.700
l 4	0.081 $\lambda$ , 50.69 $\Omega$	21.59 x 0.71	0.850 x 0.280
l 5	0.040 $\lambda$ , 4.85 $\Omega$	8.89 x 17.78	0.350 x 0.700
l 6	0.158 $\lambda$ , 37.73 $\Omega$	40.64 x 1.27	1.600 x 0.050
l 7	0.030 $\lambda$ , 10.94 $\Omega$	5.59 x 7.11	0.220 x 0.280
l 8	0.158 $\lambda$ , 37.73 $\Omega$	40.64 x 1.27	1.600 x 0.050
l 9	0.030 $\lambda$ , 10.94 $\Omega$	5.59 x 7.11	0.220 x 0.280
l 10	0.025 $\lambda$ , 5.58 $\Omega$	5.59 x 15.24	0.220 x 0.600
l 11	0.105 $\lambda$ , 5.58 $\Omega$	23.62 x 15.24	0.930 x 0.600
l 12	0.006 $\lambda$ , 5.58 $\Omega$	1.27 x 15.24	0.050 x 0.600
l 13	0.104 $\lambda$ , 21.37 $\Omega$	25.4 x 3.05	1.000 x 0.120
l 14	0.014 $\lambda$ , 50.69 $\Omega$	3.81 x 0.71	0.150 x 0.028

Reference Circuit (cont.)



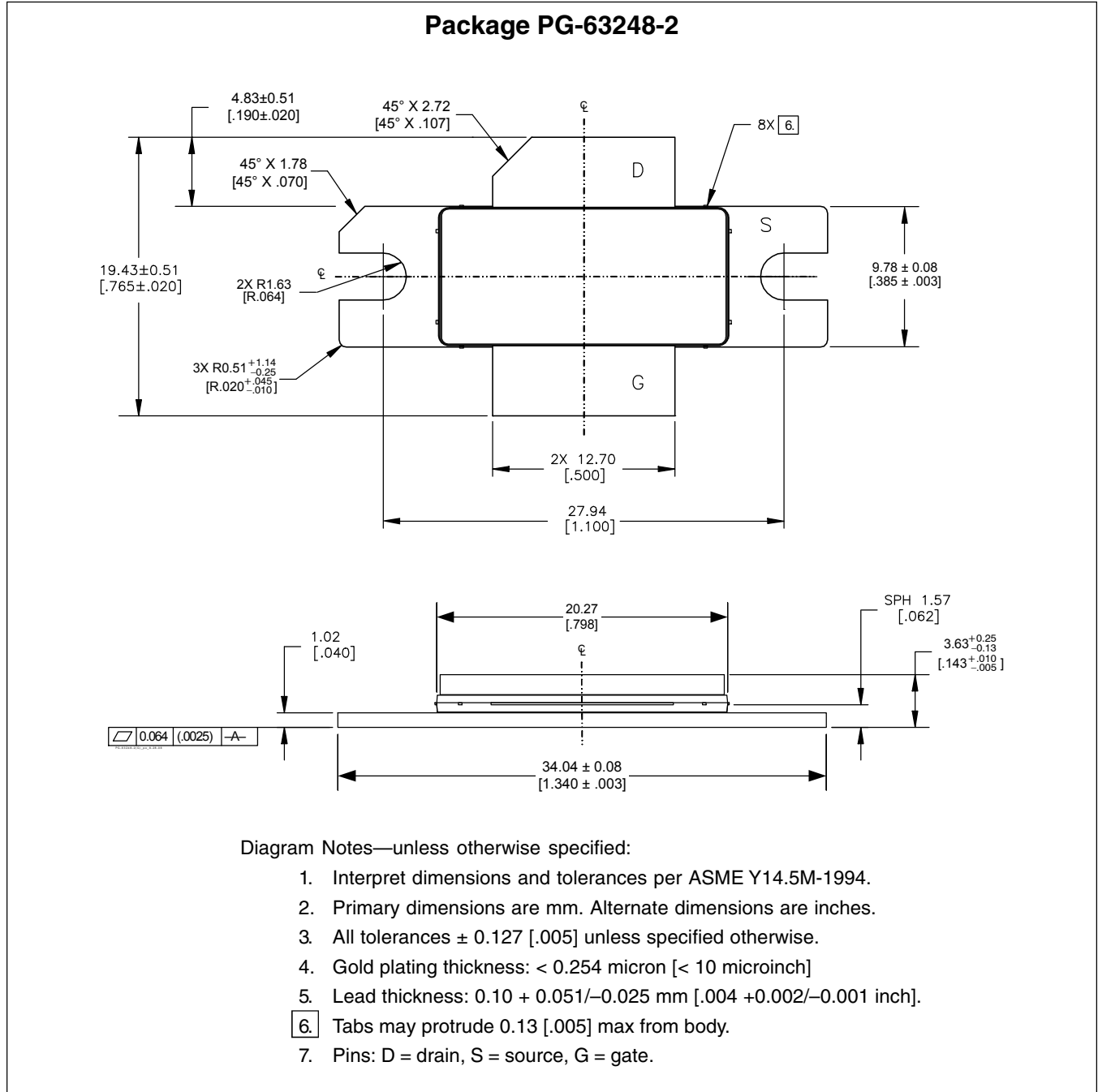
Reference circuit assembly diagram (not to scale). Gerber files for this circuit available on request.

### Reference Circuit (cont.)

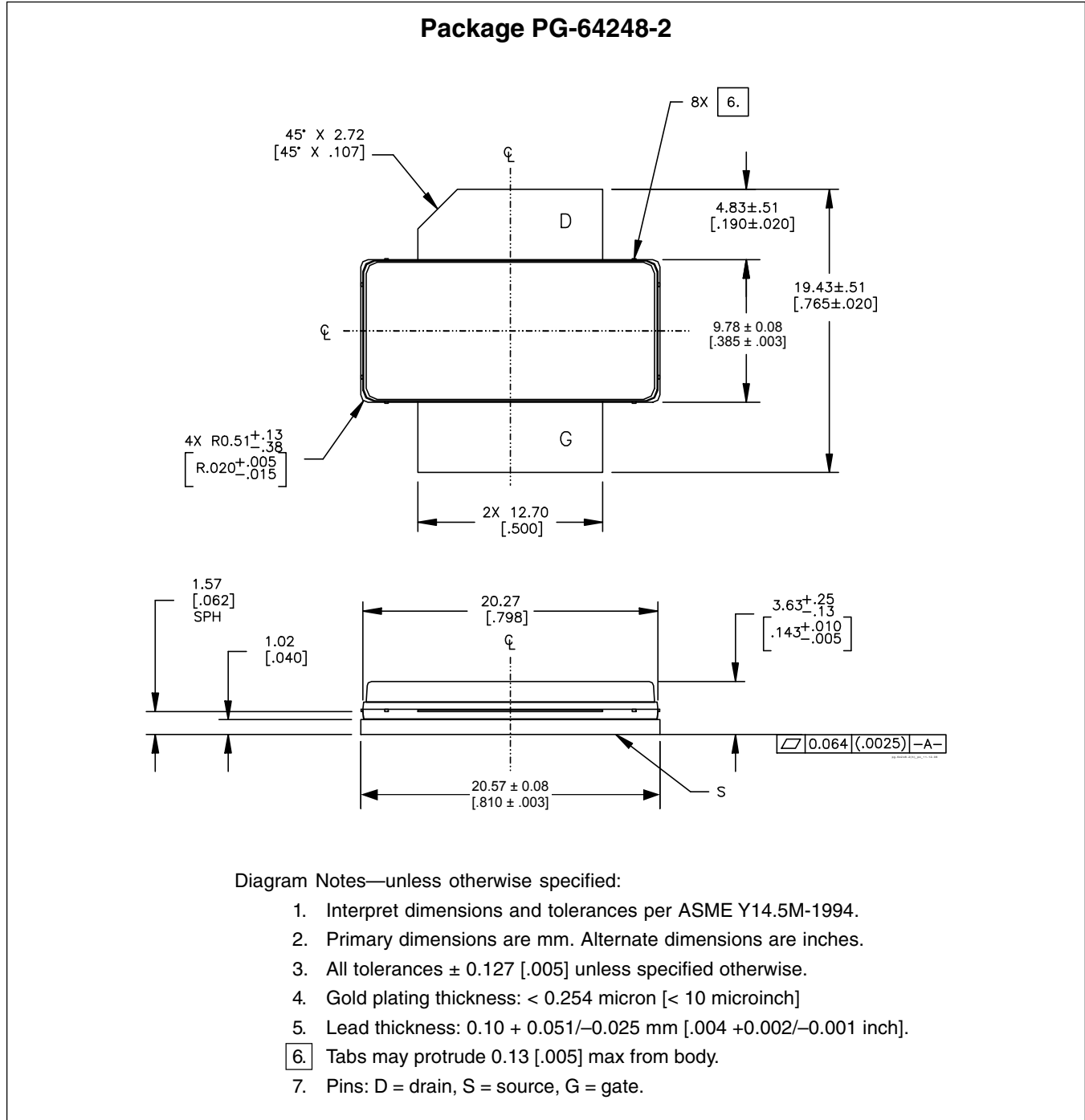
Component	Description	Suggested Manufacturer	P/N or Comment
C1, C2, C3	Capacitor, 0.001 $\mu$ F	Digi-Key	PCC1772CT-ND
C4	Tantalum capacitor, 10 $\mu$ F, 35 V	Digi-Key	PCS6106TR-ND
C5, C13, C18	Capacitor, 0.1 $\mu$ F	Digi-Key	P4525-ND
C6	Ceramic capacitor, 120 pF	ATC	100B 121
C7, C10, C15, C25	Ceramic capacitor, 100 pF	ATC	100B 101
C8, C22, C23	Ceramic capacitor, 11 pF	ATC	100B 110
C9	Ceramic capacitor, 4.3 pF	ATC	100B 4R3
C11, C16	Capacitor, 1.0 $\mu$ F	ATC	920C105
C12, C14, C17, C19	Capacitor, 10 $\mu$ F, 50 V	Garrett Electronics	TPS106K050R0400
C20	Ceramic capacitor, 5.6 pF	ATC	100B 5R6
C21	Ceramic capacitor, 5.1 pF	ATC	100B 5R1
C24	Ceramic capacitor, 8.2 pF	ATC	100B 8R2
L1, L2	Ferrite, 6 mm	Ferroxcube	53/3/4.6-452
Q1	Transistor	Infineon Technologies	BCP56
QQ1	Voltage regulator	National Semiconductor	LM7805
R1	Chip resistor, 1.2k ohms	Digi-Key	P1.2KGCT-ND
R2	Chip resistor, 1.3k ohms	Digi-Key	P1.3KGCT-ND
R3	Chip resistor, 2k ohms	Digi-Key	P2.0KECT-ND
R4	Potentiometer, 2k ohms	Digi-Key	3224W-202ETR-ND
R5	Chip resistor, 3.3k ohms	Digi-Key	P3.3KECT-ND
R6	Chip resistor, 10 ohms	Digi-Key	P10ECT-ND
R7	Chip resistor, 5.1k ohms	Digi-Key	P5.1KECT-ND



### Package Outline Specifications



Package Outline Specifications (cont.)



Find the latest and most complete information about products and packaging at the Infineon Internet page <http://www.infineon.com/rfpower>

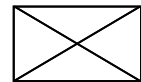
Page	Subjects (major changes since last revision)
9, 10	Clarify package information

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